

**G2N4403****PNP EPITAXIAL PLANAR TRANSISTOR****Description**

The G2N4403 is designed for general purpose switching and amplifier applications.

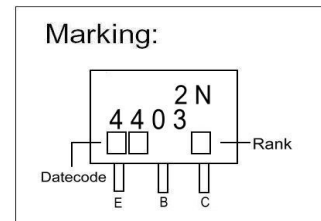
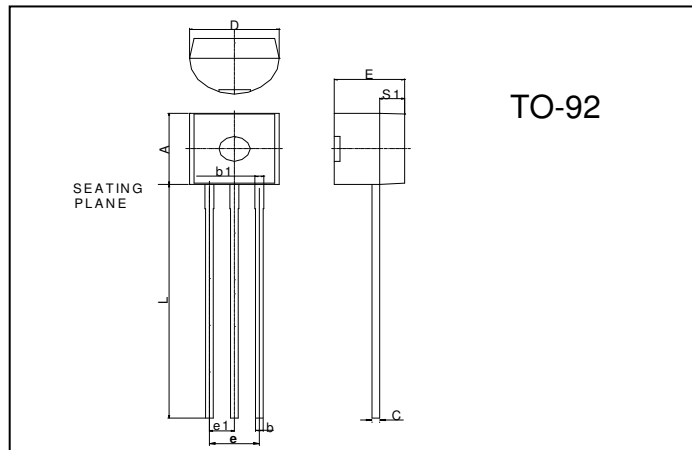
**Features**

\*Complementary to G2N4401

\*High Power Dissipation: 625mW at 25°C

\*High DC Current Gain: 100-300 at 150mA

\*High Breakdown Voltage: 40V Min

**Package Dimensions**

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

**Absolute Maximum Ratings at Ta = 25°C**

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	-40	V
Collector to Emitter Voltage	VCEO	-40	V
Emitter to Base Voltage	VEBO	-5	V
Collector Current	IC	-600	mA
Total Power Dissipation	PD	625	mW

**Characteristics at Ta = 25°C**

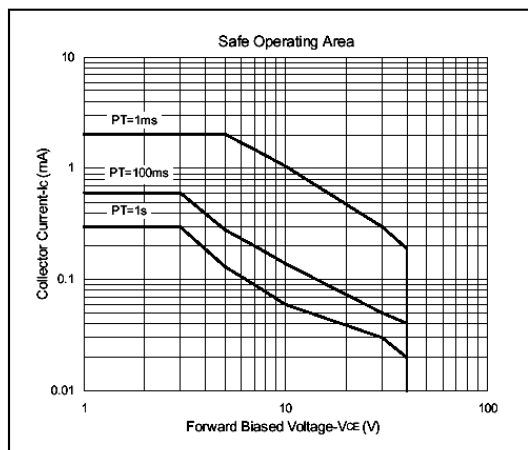
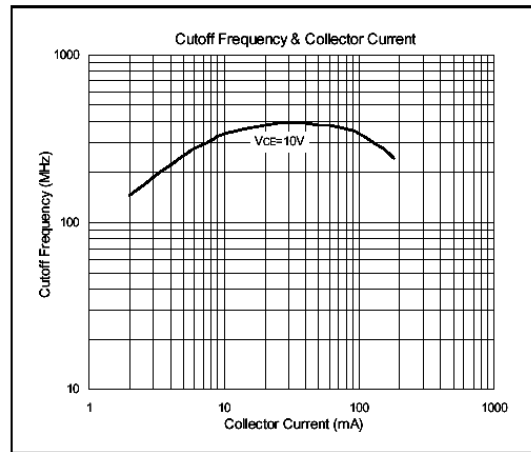
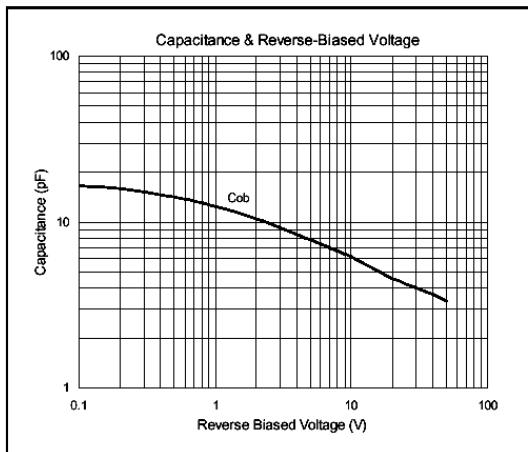
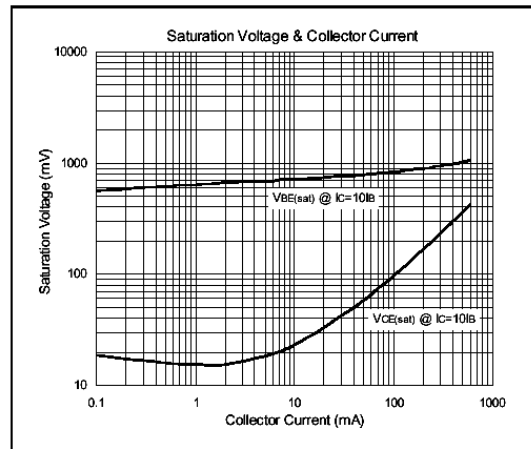
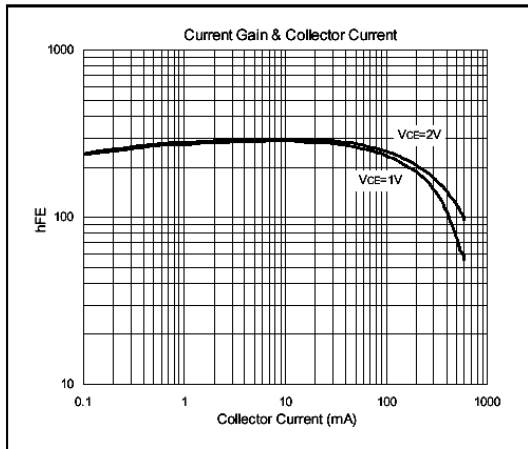
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-40	-	-	V	IC=-100uA
BVCEO	-40	-	-	V	IC=-1mA
BVEBO	-5	-	-	V	IE=-10uA
ICEX	-	-	-100	nA	VCE=-35V, VBE=-0.4V
*VCE(sat)1	-	-	-0.4	V	IC=-150mA, IB=-15mA
*VCE(sat)2	-	-	-750	mV	IC=-500mA, IB=-15mA
*VBE(sat)1	-750	-	-950	mV	IC=-150mA, IB=-15mA
*VBE(sat)2	-	-	-1.3	V	IC=-500mA, IB=-50mA
*hFE1	30	-	-		VCE=-1V, IB=-0.1mA
*hFE2	60	-	-		VCE=-1V, IC=-1mA
*hFE3	100	-	-		VCE=-1V, IC=-10mA
*hFE4	100	-	300		VCE=-2V, IC=-150mA
*hFE5	20	-	-		VCE=-2V, IC=-500mA
fT	200	-	-	MHz	VCE=-10V, IC=-20mA, f=100MHz
Cob	-	-	8.5	pF	VCB=-10V, f=1MHz

**Classification OF hFE4**

\* Pulse Test: Pulse Width ≤ 380us, Duty Cycle ≤ 2%

Rank	A	B
Range	100-210	190-300

## Characteristics Curve



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